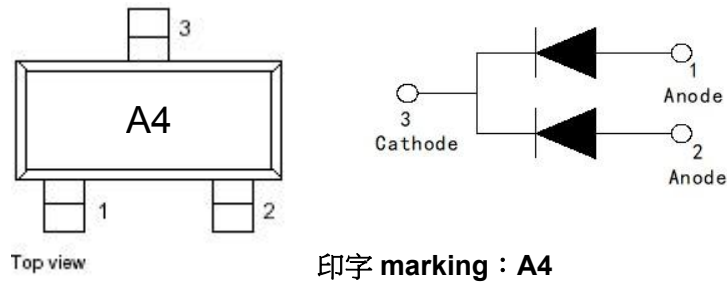


一、Features 产品特性

MAXIMUM RATINGS(T_a=25°C) 最大额定值

CHARACTERISTIC 特性参数	Symbol 符号	Rating 额定值	Unit 单位
Continuous Reverse Voltage 连续反向电压	V _R	70	Vdc
Peak Forward Current 正向峰值电流	I _F	200	mAdc
Peak Forward Surge Current 正向最大浪涌电流	I _{FM(surge)}	500	mAdc

THERMAL CHARACTERISTICS 热特性

CHARACTERISTIC 特性参数	Symbol 符号	Max 最大值	Unit 单位
Total Device Dissipation FR-5 Board(1) T _A =25°C	PD	225	mW
Total Device Dissipation Alumina Substrate,(2) T _A =25°C 总耗散功率 氧化铝衬底	P _D	300	mW
Junction and Storage Temperature 结温和储存温度	T _J , T _{stg}	150, -55 ~150	°C

- FR-5=1.0×0.75×0.062in, printed-circuit board.
- Alumina=0.4×0.3×0.024in, 99.5%alumina

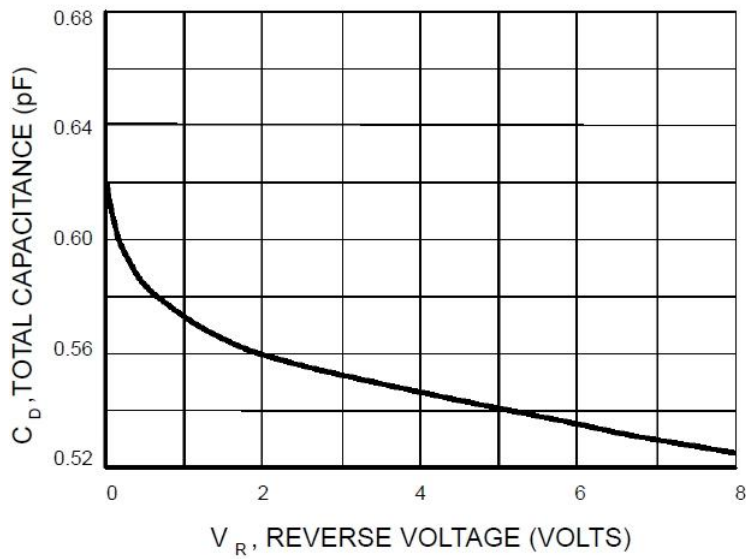
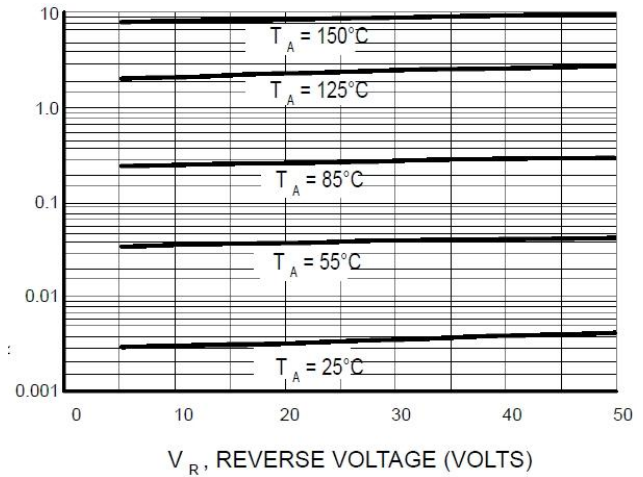
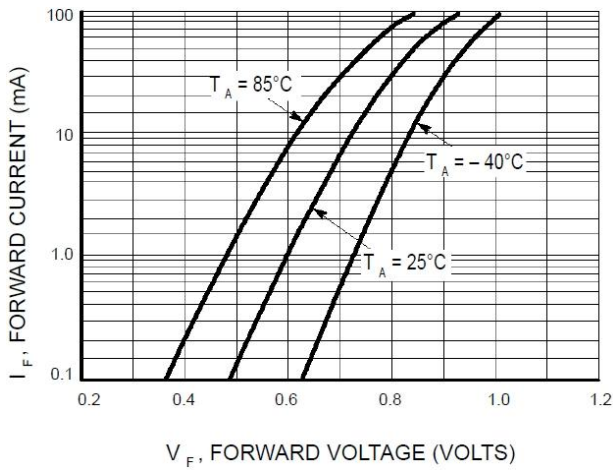
ELECTRICAL CHARACTERISTICS 电特性

(T_A=25°C unless otherwise noted 如无特殊说明, 温度为 25°C)

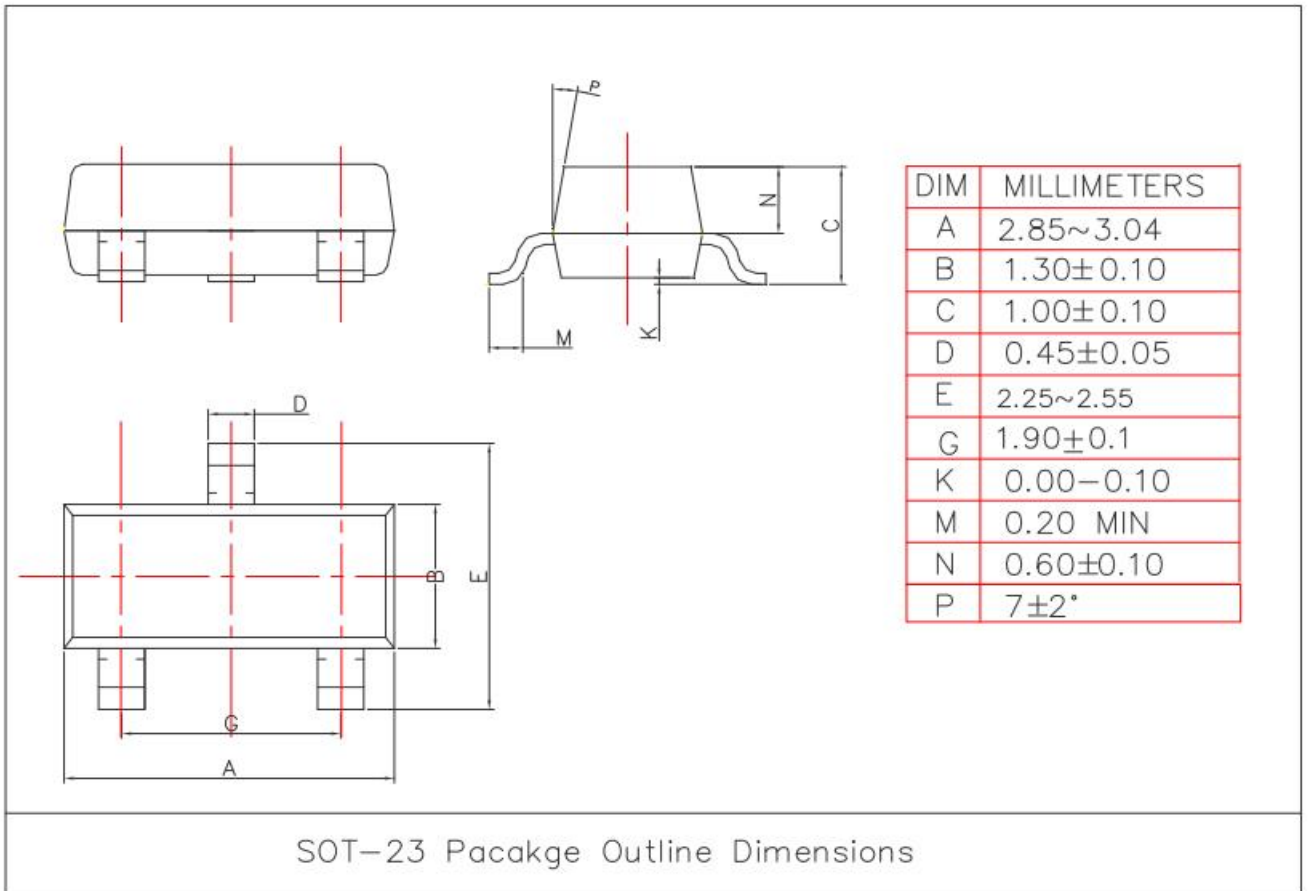
Characteristic 特性参数	Symbol 符号	Test Condition 测试条件	Min 最小值	Type 典型值	Max 最大值	Unit 单位
Reverse Voltage Leakage Current 反向漏电流	I _R	V _R =70Vdc	—	—	2.5	μA
		V _R =70Vdc, T _j =150°C	—	—	50	
		V _R =25Vdc, T _j =150°C	—	—	30	
Reverse Breakdown Voltage 反向击穿电压	V _(BR)	I _{BR} =100μAdc	70	—	—	Vdc
Forward Voltage 正向电压	V _F	I _F =1mAdc	—	—	715	mV
		I _F =10mAdc	—	—	855	
		I _F =50mAdc	—	—	1000	

		$I_F=150\text{mA dc}$	—	—	1250	
Diode Capacitance 电容	C_D	$V_R=0, f=1.0\text{MHz}$	—	—	1.5	pF
Forward Recovery Voltage 正向恢复电压	V_{FR}	$I_F=10\text{mA dc}, t_r=20\text{ns}$	—	—	1.75	Vdc
Reverse Recovery Time 反向恢复时间	t_{rr}	$I_F=I_R=10\text{mA dc}, R_L=100\Omega$	—	—	6.0	nS

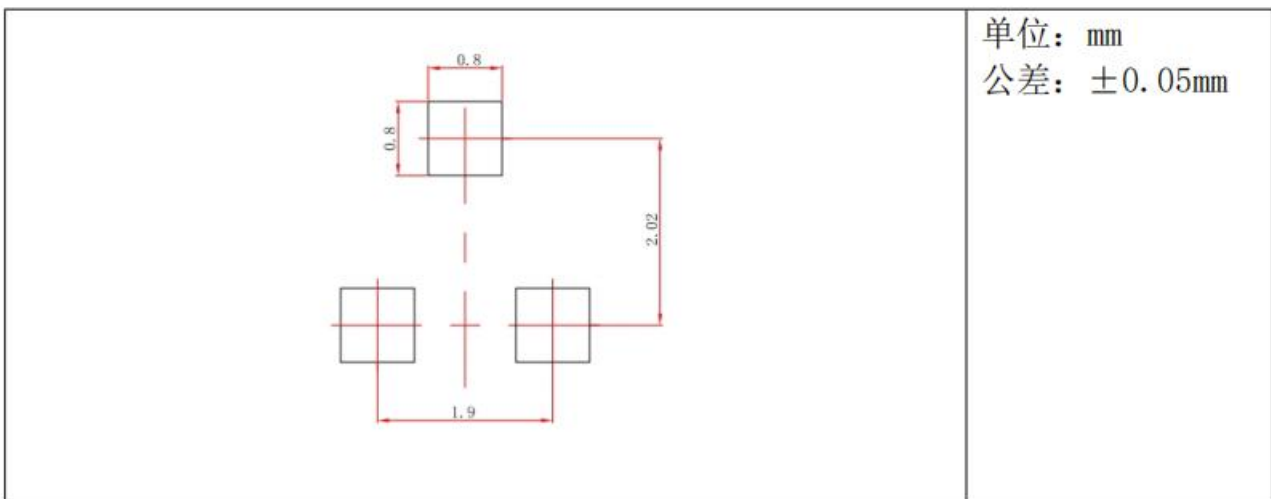
Typical Performance Characteristics



二、SOT-23 外形尺寸 (SOT-23 DIMENSION)

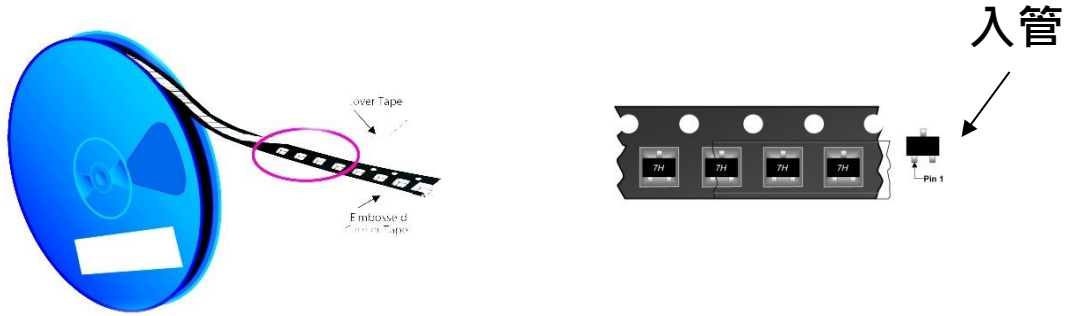


三、焊盘尺寸设计 SOT-23 Suggested Layout

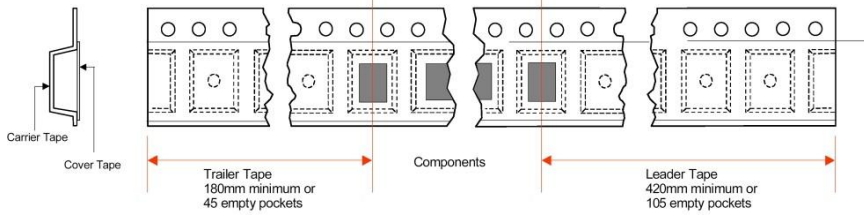


四、包装方式 Packings

封装形式	卷盘尺寸	只/卷	内盒尺寸	卷盘/内盒	只/内盒	外箱尺寸	内盒/外箱	只/外箱
SOT-23	7"	3000	190X190X135mm	10	30000	430 X 400 X 215mm	6	180K
			203X203X195mm	15	45000	440 X 440 X 230mm	4	180K



SOT-23 产品编带、包装图



SOT-23 带尾、带头空封数

